ABSTRACT OF THE DISCLOSURE

ETCHING SOLUTION FOR SELECTIVELY REMOVING SILICON NITRIDE DURING MANUFACTURE OF A SEMICONDUCTOR DEVICE

Described herein is an etching solution comprising water, phosphoric acid solution (aqueous), and a hydroxyl group-containing solvent. Such compositions are useful for the selective removal of silicon nitride over silicon oxide from a microelectronic device having such material(s) thereon during its manufacture.

(No drawing to be published)